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Substitute for form 1449A/PTO				<div> <div>Complete if Known</div> <div> <div>Application Number</div> <div>Filing Date</div> <div>First Named Inventor</div> <div>Group Art Unit</div> <div>Examiner Name</div> <div>Attorney Docket Number</div> </div> <div> <div>Concurrently Herewith</div> <div>Rama I. Hegde</div> <div>SC11697TP</div> </div> </div>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>					
Sheet	1	of	2		

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Examiner Signature	Asstt. Umar Saadhar	Date Considered	3/21/03
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Signature	<u>Asya Kymmal Joonas</u>	Considered	<input checked="" type="checkbox"/>	Not considered	<input type="checkbox"/>
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English Language Translation is attached.

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		Application Number			
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		First Named Inventor	Rama I. Hegde		
		Group Art Unit			
Examiner Name					
Sheet	2	of	2	Attorney Docket Number	SC11697TP

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
AKS	AI	D. Prot et al., "Self-diffusion in α -Al ₂ O ₃ IL Oxygen diffusion in 'undoped' single crystals", 1996 Taylor & Francis Ltd., Philosophical Magazine A, 1996, Volume 73, No. 4, pgs 899-917.	
AKS	AJ	H. Bender et al., "Physical Characterisation of High-k Gate Stacks Deposited on HF-Last Surfaces", IWGI 3002, Tokyo, pgs. 1-7.	
AKS	AK	R.J. Carter et al., "Electrical Characterisation of High-K Materials Prepared by Atomic Layer CVD", IWGI 2001, Tokyo, pgs. 1-6.	
AKS	AL	L. Manchanda et al., "Multi-component high-K gate dielectrics for the silicon industry", Elsevier Science B.V., pgs. 351-359.	
AKS	AM	V.V. Afanas'ev ^a et al., "Energy barriers between (100)Si and Al ₂ O ₃ and ZrO ₂ -based dielectric stacks: internal electron photoemission measurements", 2001 Elsevier Science B.V. All rights reserved, pgs. 335-339.	
AKS	AN	Massimo Fischetti et al., "IBM Research Report", RC 22092 (99048) June 12, 2001, pgs. 1-25.	
AKS	AO	D.A. Neumayer et al., "Materials characterization of ZrO ₂ -SiO ₂ and HfO ₂ -SiO ₂ binary oxides deposited by chemical solution deposition", 2001 American Institute of Physics, Journal of Applied Physics, Vol. 90, No. 4, August 15, 2001, pgs. 1801-1808.	
AKS	AP	Toyokazu Tambo et al., "Molecular Beam Epitaxy of SrTiO ₃ Films on Si(100)-2x1 with SrO Buffer Layer", 1998 Publication Board, Japanese Journal of Applied Physics, Jpn. J. Appl. Phys. Vol. 37 (1998), pgs 4454-4459.	

Examiner Signature	Asish Kumar Sarker	Date Considered	3/21/03
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